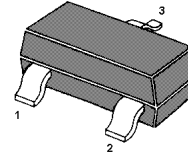


PNP Silicon Epitaxial Planar Transistor

for use in FM RF amplifier, mixer, oscillators, converters and IF amplifiers applications

The transistor is subdivided into three groups, R, Q and Y according to its DC current gain.



1.Base 2.Emmitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	30	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$ Current Gain Group	R h_{FE}	60	-	120	-
	Q h_{FE}	90	-	180	-
	Y h_{FE}	135	-	270	-
Collector Cutoff Current at $-V_{CB} = 10\text{ V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	0.1	μA
Transition Frequency at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$	f_T	150	230	-	MHz
Reverse Transfer Capacitance at $-V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{re}	-	-	1.7	pF
Noise Figure at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$, $f = 100\text{ MHz}$	NF	-	2.5	-	dB

